a

3D FET array

Exploded view

PI
Si
PMMA
Au
PI
SU8
PR
Si
PMMA

Bending gold loop

Si/Au contact

One FET inside one cell

Lightly doped
FET

Two FETs inside one cell

b

2D precursor

Hinges

3D device

c

Mechanical analysis after device folded up

ε_{max-Au} (%)
0   5

ε_{max-Si} (%)
0.0   0.1

d

Topography

Height (nm)
0   90   180   270   360   450

Conductivity (uncali.)

Normalized magnitude (dB)
0.0   0.2   0.4   0.6   0.8   1.0